



### 0.2A SCHOTTKY BARRIER DIODE CHIP SCALE PACKAGE

### **Product Summary**

V <sub>RRM</sub> (V)	I <sub>O</sub> (mA)	V <sub>F</sub> Max (V) @ +25°C	I <sub>R</sub> Max (μA) @ +25°C
30	200	0.50	9

### **Description**

The SDM02U30CSP is a 30-Volt 0.2A Schottky Barrier Diode that is optimized for low forward voltage drop and low leakage current. It's housed in a compact Chip Scale Package (CSP) that occupies only 0.18mm<sup>2</sup> board space. The low thermal resistance enables designers to meet design challenges of increasing efficiency while reducing board space. It is ideally suited for use in portable applications.

# **Applications**

- Blocking Diode
- Reverse Protection Diode
- Boost Diode

### **Features and Benefits**

- 0.18mm<sup>2</sup> Footprint, Off Board Profile of 0.28mm
- Low Forward Voltage of 0.50V (Max) Minimizes Power Dissipation Losses
- Low Leakage Maximizes Battery Power
- Soft, Fast Switching Capability
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

### **Mechanical Data**

- Case: X3-WLB0603-2
- Moisture Sensitivity: Level 1 per J-STD-020
- Polarity Indicator: Cathode Dot
- Terminals: NiAu Bump. Solderable per MIL-STD-202, Method 208
- Weight: 0.1mg (Approximate)

### X3-WLB0603-2



Top View



Bottom View

## **Ordering Information** (Note 4)

Part Number	Case	Packaging
SDM02U30CSP-7	X3-WLB0603-2	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**

### X3-WLB0603-2



K = Product Type Marking Code Dot Denotes Cathode Pin



# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Single phase, half wave, 60Hz, resistive or inductive load. For capacitance load, derate current by 20%.

Characteristic	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	$V_{RRM}$	30	V
Average Rectified Output Current	lo	0.2	А
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load	I <sub>FSM</sub>	4.5	А

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Typical Thermal Resistance Junction to Ambient (Note 5)	$R_{ heta JA}$	215	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

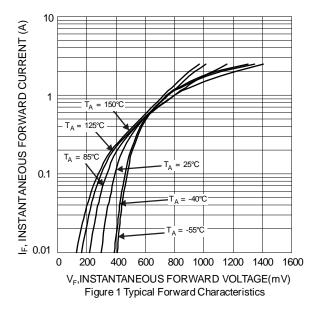
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
	V <sub>F</sub>	_	0.24	0.29	V	I <sub>F</sub> = 1mA, T <sub>J</sub> = +25°C
		_	0.30	0.34		$I_F = 10 \text{mA}, T_J = +25 ^{\circ}\text{C}$
Forward Voltage Drop		_	0.40	0.46		I <sub>F</sub> = 100mA, T <sub>J</sub> = +25°C
		_	0.45	0.50		I <sub>F</sub> = 200mA, T <sub>J</sub> = +25°C
		_	0.39	_		I <sub>F</sub> = 200mA, T <sub>J</sub> = +125°C
	I <sub>R</sub>	_	0.4	2.0	μA	V <sub>R</sub> = 10V, T <sub>J</sub> = +25°C
Leakage Current (Note 6)		_	1.5	9	μA	$V_R = 30V, T_J = +25^{\circ}C$
		_	0.7	_	mA	$V_R = 30V, T_J = +125$ °C
Junction Capacitance	C <sub>T</sub>	_	7		pF	$V_R = 10V, T_J = +25^{\circ}C, f = 1MHz$

Notes:

<sup>5.</sup> Device mounted on FR-4 substrate PC board, with minimum recommended pad layout per http://www.diodes.com/package-outlines.html. 6. Short duration pulse test used to minimize self-heating effect.



# **Typical Electrical Characteristics**



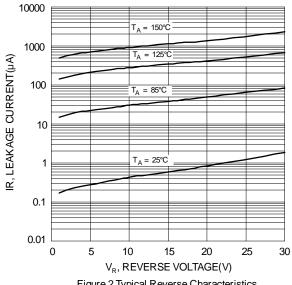
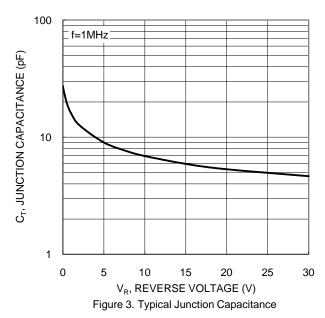


Figure 2 Typical Reverse Characteristics



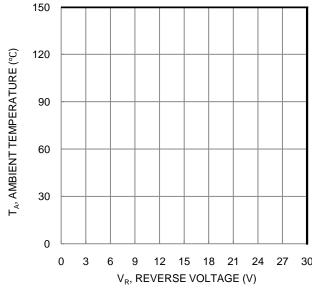


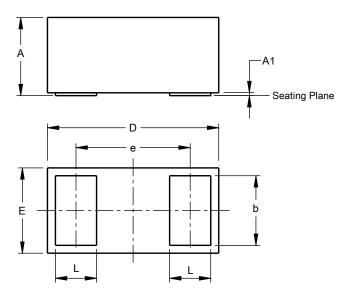
Figure 4. Operating Temperature Derating



## Package Outline Dimensions (Note 7)

Please see http://www.diodes.com/package-outlines.html for the latest version.

### X3-WLB0603-2



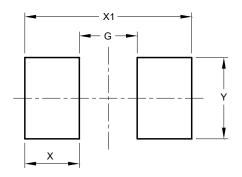
X3-WLB0603-2					
Dim	Min	Max	Тур		
Α	0.250	0.300	0.275		
A1	0.00	0.01	-		
b	0.220	0.280	0.245		
D	0.575	0.625	0.600		
Е	0.275	0.325	0.300		
е	_	_	0.400		
L	0.120	0.180	0.144		
All Dimensions in mm					

Note 7: Device side walls are electrically active bare silicon. Avoid contact of solder or flux on the side walls during the PCB assembly process.

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### X3-WLB0603-2



Dimensions	Value (in mm)	
G	0.206	
Х	0.194	
Y	0.291	
V1	0.504	



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